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Applicants: Akihiko ISHIBASHI et al.

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U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,787,104	07/28/1998	Kamiyama et al.			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
GM	0 887 436	12/30/1998	EP			Full Eng
	07-235505	09/05/1995	JP			Part Eng
	08-255932	10/01/1996	JP			X
	08-316141	11/29/1996	JP			Part Eng
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	11-074203	03/16/1999	JP			Part Eng
GM	2702889	10/03/1997	JP			X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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GM	Miyake et al., "Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy", pp. L1000-L1002, September 15, 1999, Jpn. J. Appl. Phys., Vol 38, Part 2, No. 9A/B
	Nakamura et al., "AlN and AlGaIn Growth Using Low-Pressure Metalorganic Chemical Vapor Deposition", pp. 280-285, 1998, Journal of Crystal Growth 195
	Mihopoulos, et al., "A Reaction-Transport Model for AlGaIn MOVPE Growth", pp. 733-739, 1998, Journal of Crystal Growth 195
GM	Lee et al., "Characteristics of In Ga N/GaN Grown by LPMOVPE with the Variation of Growth Temperature", pp. 6-10, 1997, Journal of Crystal Growth 182

Examiner

Date Considered

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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